Application Data Sheet

Inventor Information

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Yuichi

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Postal or Zip Code:

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Correspondence Information

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Application Information

Title:

STATIC RANDOM ACCESS MEMORY AND

SEMICONDUCTOR DEVICE USING MOS TRANSISTORS HAVING CHANNEL REGION ELECTRICALLY CONNECTED

WITH GATE

Total Drawing Sheets:

5

Formal Drawings:

Yes

Application Type:

Utility

Docket Number:

204552016501

Representative Information

Representative Customer Number:

25227

Continuity Information

This application is a:

Continuation

Of application:

09/412,328

Filed: 10/5/1999

Prior Foreign Applications

Foreign Application:

10-282335

Filing Date:

10/05/1998

Japan

Country:
Priority Claimed:

Yes

Assignee Information

Company Name:

Sharp Kabushiki Kaisha

Address Line One:

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Address Line Two:

Osaka

City: Country:

Japan

Postal or Zip Code: